

Title (en)
SEMICONDUCTOR MEMORY DEVICE

Publication
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Application
EP 86400504 A 19860311

Priority
• JP 4935085 A 19850314
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Abstract (en)
[origin: EP0194939A2] A semiconductor memory device of multi-bit type which produces plural output signals ($O_{1</sub>}, \dots, O_{8</sub>}$ corresponding to read-out data from one address at a time including memory means for storing data. In a plurality of output buffer stages for producing the output signals, the operation of the output buffer stages is based upon at least a timing signal. Means (151, ..., 158) for operating the output buffer stages have predetermined time differences. The output signals ($O_{1</sub>}, \dots, O_{8</sub>}$ having predetermined time differences are delivered from the output buffer stages.

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G11C 7/00

IPC 8 full level
G11C 7/10 (2006.01); **G11C 7/22** (2006.01)

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G11C 11/34 (2013.01 - KR)

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US 4635234 A 19870106 - YAMAGUCHI TAKASHI [JP]

Cited by
EP0316082A3; EP0686975A1

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DE FR GB

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